Elektronische Bauelemente

SSP7431P

-17A, -30V, $R_{DS(ON)}$ 13 mΩ
P-Channel Enhancement MOSFET

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $R_{DS(on)}$ and to ensure minimal power loss and heat dissipation.

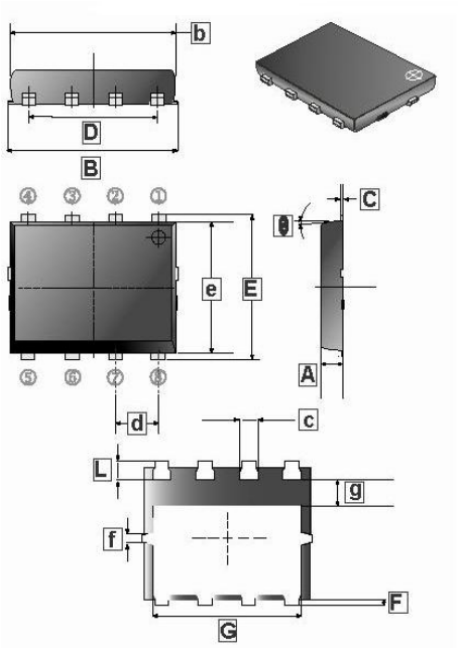
FEATURES

- Low $R_{DS(on)}$ provides higher efficiency and extends battery life.
- Low thermal impedance copper leadframe SOP-8PP saves board space.
- Fast switching speed.
- High performance trench technology.

APPLICATION

DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

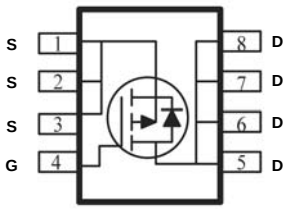
SOP-8PP



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.85	1.00	θ	0°	10°
B	5.3 BSC.		b	5.2 BCS	
C	0.15	0.25	c	0.30	0.50
D	3.8 BCS.		d	1.27BSC	
E	6.05 BCS.		e	5.55 BCS.	
F	0.03	0.30	f	0.10	0.40
G	4.35 BCS.		g	1.2 BCS.	
L	0.40	0.70			

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOP-8PP	3K	13 inch



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise specified)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1]	T_A=25°C	I_D	-17	A
	T_A=70°C		-14	
Pulsed Drain Current [2]		I_{DM}	-50	A
Continuous Source Current (Diode Conduction) [1]		I_S	-2.1	A
Power Dissipation [1]	T_A=25°C	P_D	5.0	W
	T_A=70°C		3.2	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Thermal Resistance Rating				
Maximum Junction to Ambient [1]	t≦10 sec	$R_{\theta JA}$	25	°C / W
	Steady-State		65	

Notes:
1. Surface Mounted on 1" x 1" FR4 Board.
2. Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Teat Conditions
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	-30	-	-	V	V_{GS}=0, I_D = -250μA
Gate-Threshold Voltage	$V_{GS(th)}$	-1	-	-	V	V_{DS}=V_{GS}, I_D = -250μA
Gate-Body Leakage	I_{GSS}	-	-	±100	nA	V_{DS}=0, V_{GS}= ±25V
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1	μA	V_{DS}= -24V, V_{GS}=0
		-	-	-5		V_{DS}= -24V, V_{GS}=0, T_J=55°C
On-State Drain Current [1]	$I_{D(ON)}$	-50	-	-	A	V_{DS}= -5V, V_{GS}= -10V
Drain-Source On-Resistance [1]	$R_{DS(ON)}$	-	-	13	mΩ	V_{GS}= -10V, I_D= -11.5A
		-	-	19		V_{GS}= -4.5V, I_D= -9.3A
Forward Transconductance [1]	g_{FS}	-	29	-	S	V_{DS}= -15V,,I_D= -11.5A
Diode Forward Voltage	V_{SD}	-	-0.8	-	V	I_S=2.5A, V_{GS}=0
Dynamic [2]						
Total Gate Charge	Q_g	-	25	-	nC	I_D= -11.5A V_{DS}= -15V V_{GS}= -5V
Gate-Source Charge	Q_{gs}	-	11	-		
Gate-Drain Charge	Q_{gd}	-	17	-		
Turn-On Delay Time	$Td_{(ON)}$	-	15	-	nS	I_D= -1A, V_{DD}= -15V V_{GEN}= -10V R_L=6Ω
Rise Time	T_r	-	13	-		
Turn-Off Delay Time	$Td_{(OFF)}$	-	100	-		
Fall Time	T_f	-	54	-		

Notes:
1. Pulse test：PW ≦ 300 μs duty cycle ≦ 2%.
2. Guaranteed by design, not subject to production testing.

CHARACTERISTIC CURVES

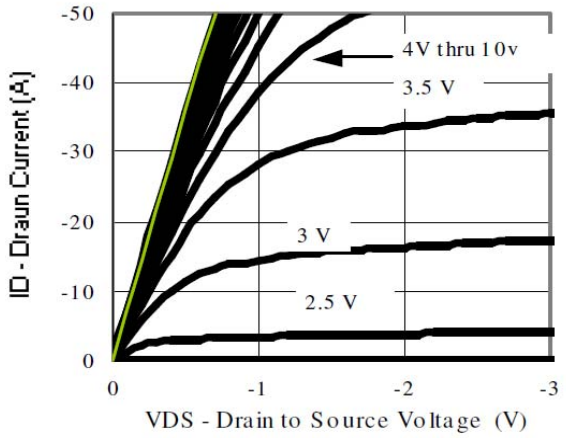


Figure 1. On-Region Characteristics

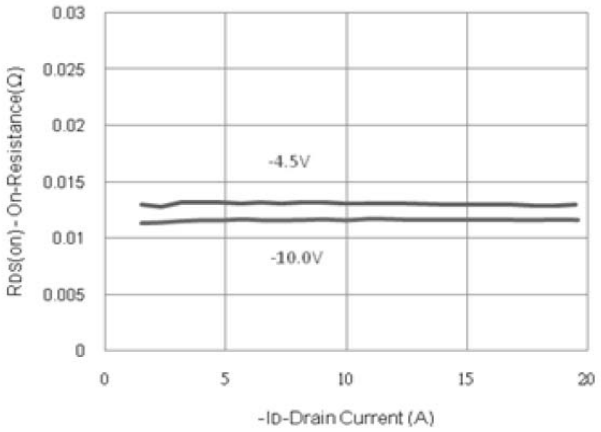


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

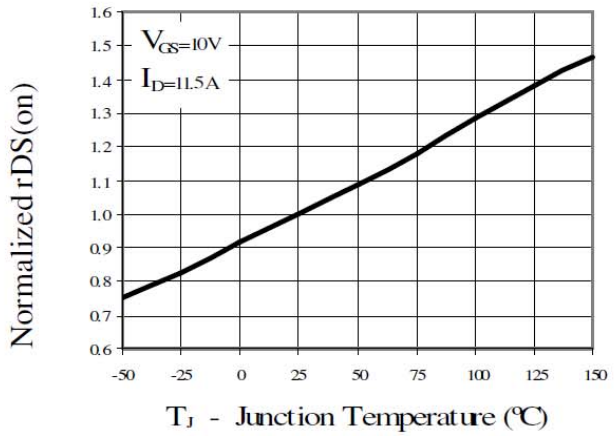


Figure 3. On-Resistance Variation with Temperature

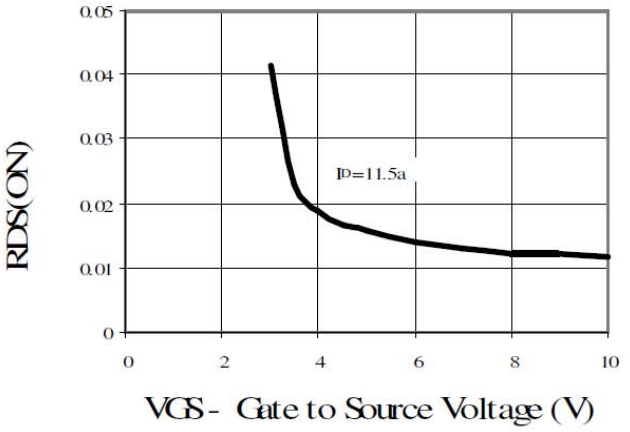


Figure 4. On-Resistance with Gate to Source Voltage

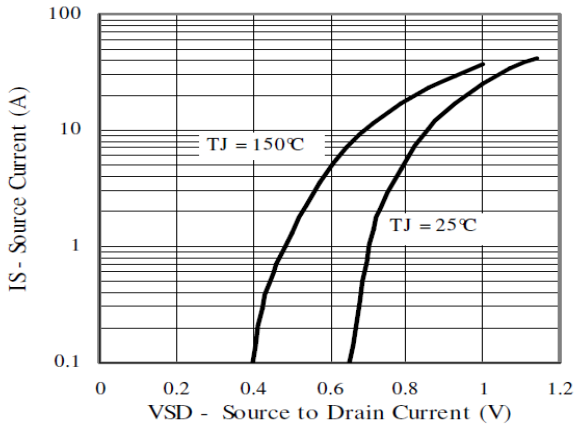


Figure 5. Transfer Characteristics

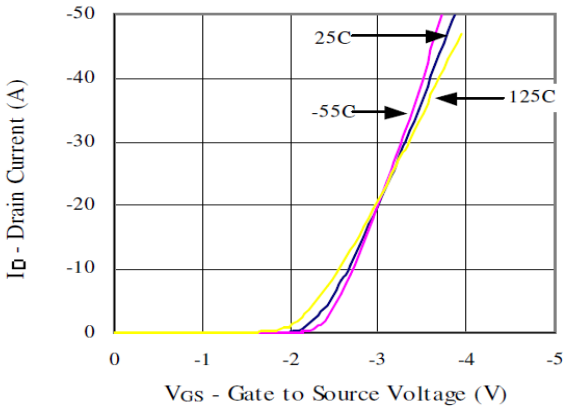


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

CHARACTERISTIC CURVES

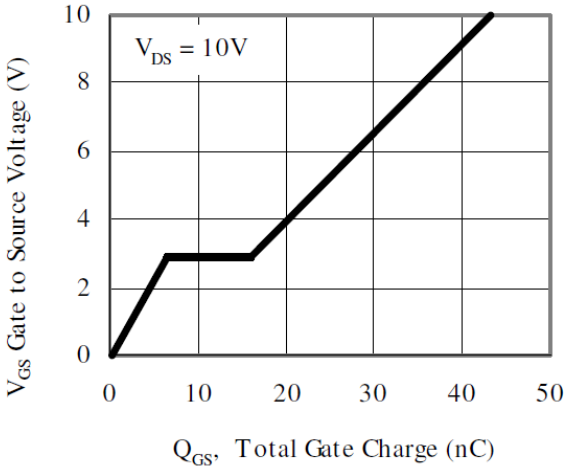


Figure 7. Gate Charge Characteristics

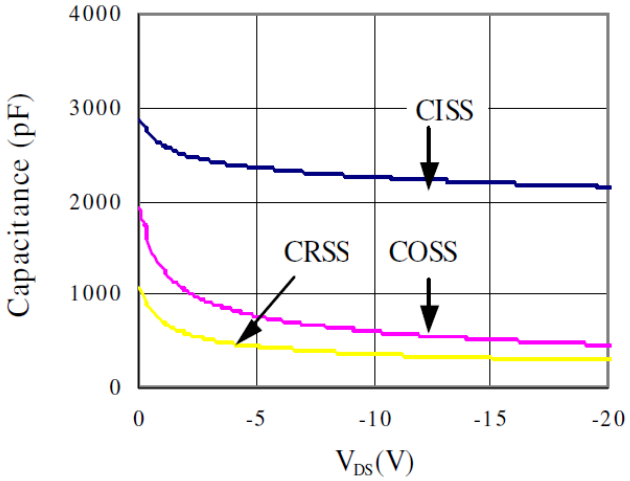


Figure 8. Capacitance Characteristics

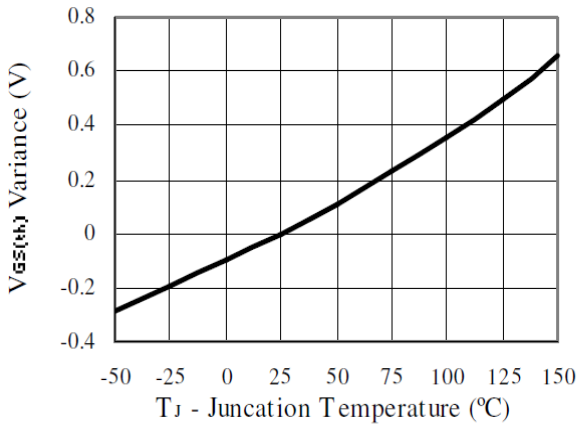


Figure 9. Maximum Safe Operating Area

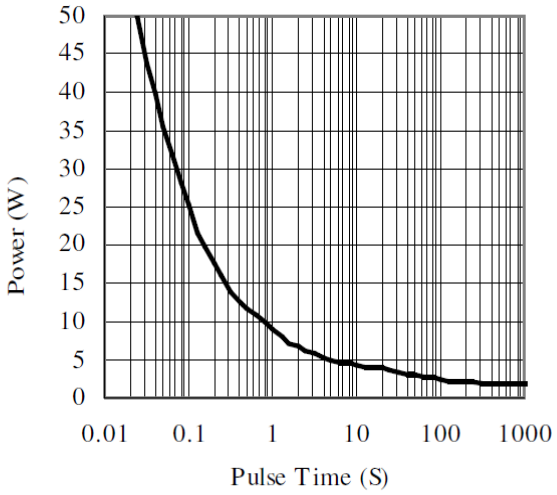


Figure 10. Single Pulse Maximum Power Dissipation

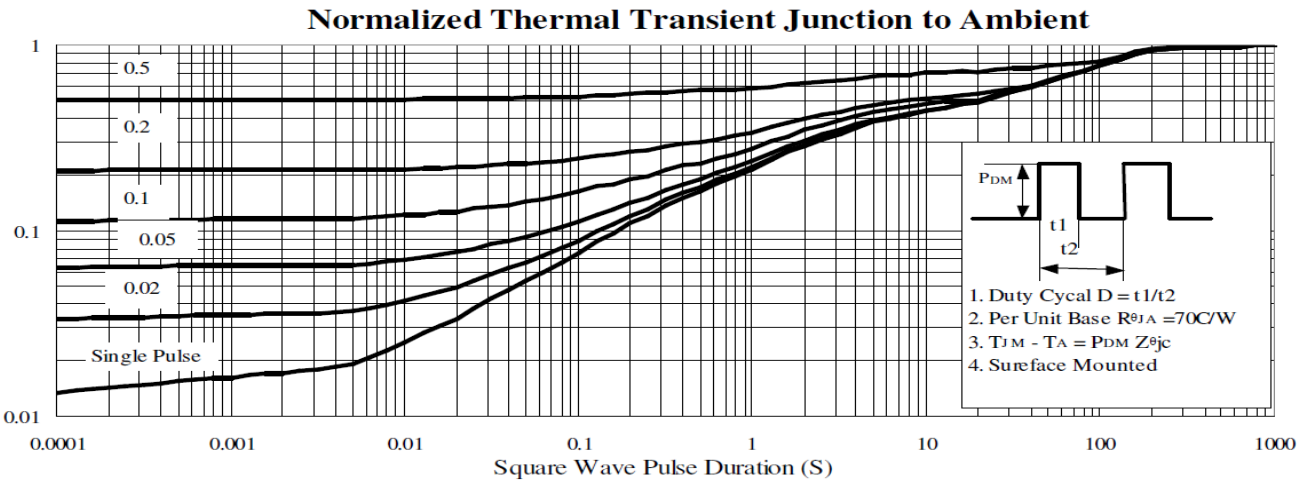


Figure 11. Transient Thermal Response Curve